

NTSP1

Application Specific Discretes A.S.D.™

NETWORK TERMINATION S INTERFACE PROTECTION

MAIN APPLICATIONS

ISDN equipment where transient overvoltage and electrostatic discharge protection is required, such as:

- S interface on NT equipment
- S interface of terminal equipment

DESCRIPTION

The NTSP1 is a monolithic diode structure especially designed to protect ISDN S/T interfaces against transient overvoltage and ESD surges.

FEATURES

Peak pulse current: IPP = 10 A max (5 / 310 μs)
 Clamping voltage: V_{CL} = 3 V max

Low leakage current: I_R = 1 μA
 Capacitance: C = 40 pF typ.

BENEFITS

- Monolithic diode structure for high reliability
- Transient overvoltage and ESD surges protection
- Board space saving

COMPLIES WITH THE FOLLOWING STANDARDS:

CCITT K21 1 kV, 10/700 us

(with serial resistance of 100Ω)

see test circuit

CCITT K22 1 kV, 1.2/50 μs

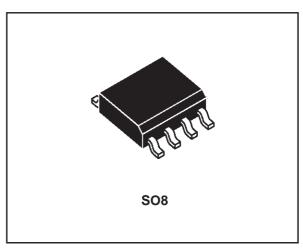
(with serial resistance of 50Ω)

IEC 1000-4-5 2 kV, 1.2/50 μs

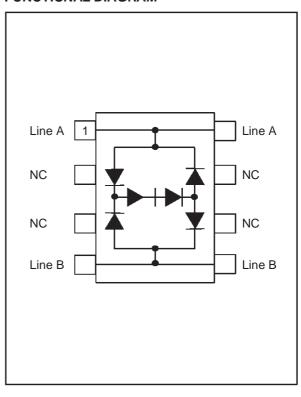
(with serial resistance of 100Ω)

IEC 1000-4-2 15 kV (air discharge)

8 kV (contact discharge)

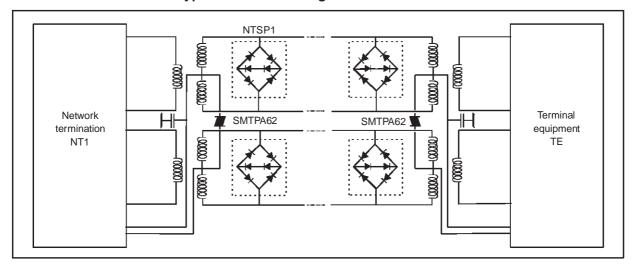


FUNCTIONAL DIAGRAM



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APPLICATION EXAMPLE: typical connection diagram



ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25 \, ^{\circ}C$)

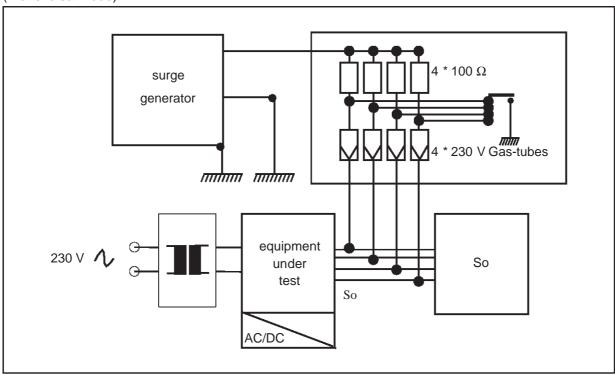
Symbol	Parameter	Test condition	Value	Unit
I _{PP}	Peak pulse current	1 kV 10/700 μs (see test circuit) 2 kV 1.2/50 μs (see test circuit)	10 20	А
T _{stg}	Storage temperature range		-40 to +150	°C
T∟	Lead temperature for soldering during 10 s		260	°C

ELECTRICAL CHARACTERISTICS (T_{amb} = 25 °C)

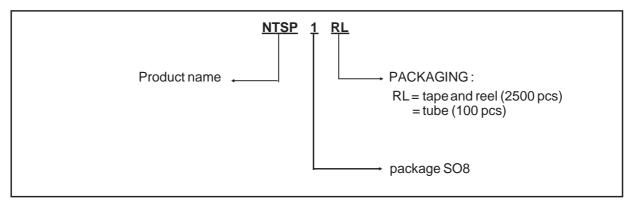
Туре	Parameter	Test condition	Тур.	Max.	Unit
V _{CL}	Clamping voltage	1 mA, measured at 50 Hz at I _{PP} , 10/700 μs at I _{PP} , 1.2/50 μs		3 15 25	V
I _R	Leakage current	V _R = 1.2 V, 25 °C V _R = 1.2 V, 70 °C		1 5	μA μA
С	Capacitance	V _R = 1.2 V, F = 1 MHz	40		pF

TEST CIRCUIT

(Transversal mode)

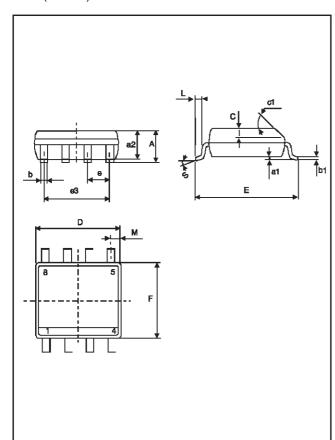


ORDER CODE



PACKAGE MECHANICAL DATA

SO8 (Plastic)



	DIMENSIONS						
REF.	Millimetres			Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
А			1.75			0.069	
a1	0.1		0.25	0.004		0.010	
a2			1.65			0.065	
b	0.35		0.48	0.014		0.019	
b1	0.19		0.25	0.007		0.010	
С		0.50			0.020		
c1			45°	(typ)			
D	4.8		5.0	0.189		0.197	
Е	5.8		6.2	0.228		0.244	
е		1.27			0.050		
еЗ		3.81			0.150		
F	3.8		4.0	0.15		0.157	
L	0.4		1.27	0.016		0.050	
М			0.6			0.024	
S	8° (max)						

Weight: 0.08g

MARKING

Туре	Marking
NTSP1	NTSP1

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